

RF & Wireless

Semiconductors



About CEL

California Eastern Laboratories (CEL) is an engineering, sales and marketing company focused on RF Semiconductors, Optical Semiconductors and Wireless Connectivity Solutions.

CEL serves designers, OEMs and contract manufacturers in various RF, Wireless and Optical markets. With over 55 years experience in high frequency design, customer support and fulfillment, CEL is ideally positioned to provide its customers with a stable supply of products to meet their specific needs.

CEL maintains extensive inventories and provides engineering and applications assistance at its technical centers in Santa Clara, CA., Wauconda, IL and Boulder, CO. The company supports customers through sales offices, sales representatives and distributors in numerous locations.



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PRODUCTS by APPLICATION

Front End Components	2
Up to 6GHz Applications	2
LNAs for 2 to 8GHz Applications	3
2.4 & 5.8GHz WLAN & WLAN Infrastructure Devices	4

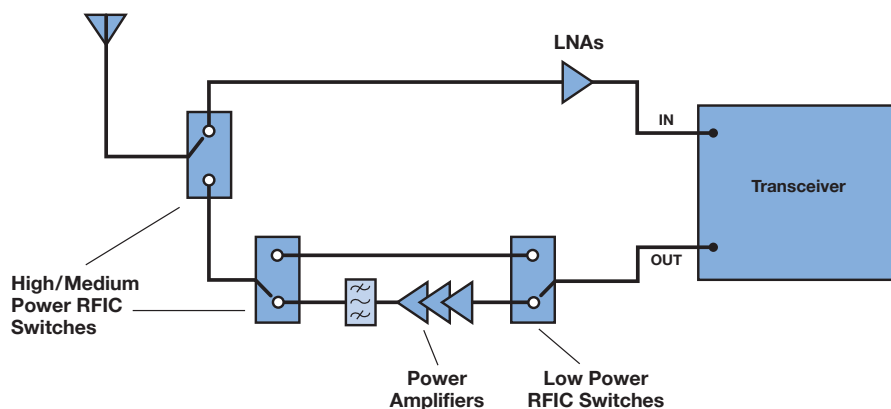
PRODUCT SPECIFICATIONS

RF Switch ICs	
SPDTs (Single Pole Double Throw)	5
SP3Ts (Single Pole Triple Throw)	6
DPDTs (Double Pole Double Throw)	6
GaAs FETs	
Low Noise GaAs FETs, 1 to 20GHz	6
Silicon MOSFET Devices	
RF Power LD-MOSFETs	7
MOSFET for Microphone Impedance Conversion	7
Silicon Bipolar Transistors	
Small Signal Silicon Devices	8
Medium Power Transistors	9
Twin Transistors	9
Silicon RFICs	
3V Silicon MMIC Amplifiers	10
5V Silicon MMIC Amplifiers	10
Frequency Upconverters	10
Frequency Downconverters	10
Package Dimensions	11
Product Longevity Program	12

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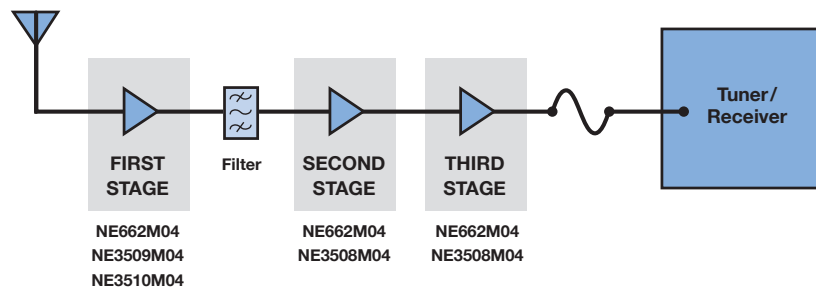
Front End Components Up to 6 GHz Applications

Wi-Fi • Bluetooth • ZigBee • Automated Meter Reading • Mesh & Home Area Networks • ISM Band applications



RFIC Switches (additional P/Ns available, see page 5)		450 MHz	915 MHz	2.4 GHz	6 GHz
UPG2409TB / T6X	SPDT, High power, wide bandwidth, SOT-363 and TSON package options	✓	✓	✓	✓
UPG2408TB / TK	SPDT, Medium power, SOT-363 and smaller package options	✓	✓	✓	
UPG2406TK	SPDT, Medium power, small package (opposite logic vs. UPG2408TX)	✓	✓	✓	
NEW CKRF2179MM26	SPDT, Medium Power, SOT-363	✓	✓	✓	
NEW CKRF2185XS02	SPDT, Medium Power, wide bandwidth, small package	✓	✓	✓	✓
UPG2164T5N	DPDT, Diversity/Transfer Switch (two selectable RF paths on)	✓	✓	✓	
Power Amplifier Transistors (additional P/Ns available, see page 7 & 9)		450 MHz	915 MHz	2.4 GHz	6 GHz
NE5550979A	+39.5dBm, 9W, 7.5V LD MOSFET	✓	✓		
NE5550234	+33dBm, 2W, 7.5V LDMOS FET	✓	✓		
NE664M04	+26dBm, 3.6V Silicon Discrete	✓	✓	✓	
NE678M04	+18dBm, 3.0 V Silicon Discrete	✓	✓	✓	
NE677M04	+15dBm, 3.0 V Silicon Discrete	✓	✓	✓	
Low Noise Amplifier Transistors		450 MHz	915 MHz	2.4 GHz	6 GHz
NE662M04	Silicon Discrete, NF = 1.1, Ga = 16.0, OIP3 = +22dBm @ 2GHz	✓	✓	✓	
NE3509M04	GaAs FET, NF = 0.40, Ga = 17.5, OIP3 = +22dBm @ 2 GHz			✓	✓
NE3508M04	GaAs FET, NF = 0.45, Ga = 14.0, OIP3 = +31dBm @ 2 GHz			✓	✓

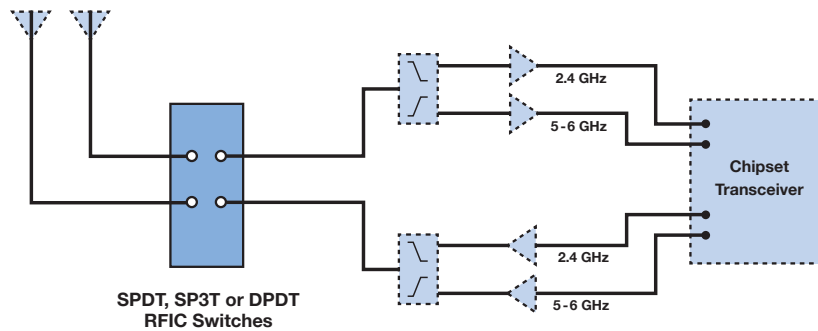
LNAs for 2 to 8GHz Applications



LNA Performance *(see Data Tables for additional specifications)*

Part Number	Description	NF (dB)	Gain (dB)	P1dB (dBm)	Package
NE662M04	Silicon Bipolar Transistor	1.1 @ 2.0GHz	16.0 @ 2.0GHz	+11.0	M04
NE3508M04	GaAs HJ-FET	0.45 @ 2.0GHz	14.0 @ 2.0GHz	+18.0	M04
NE3509M04	GaAs HJ-FET	0.40 @ 2.0GHz	17.5 @ 2.0GHz	+14.0	M04
NE3510M04	GaAs HJ-FET	0.35 @ 2.0GHz	19.0 @ 2.0GHz	+12.0	M04

2.4 & 5.8GHz WLAN & WLAN Infrastructure Devices



GaAs RFIC Switches to 3GHz

UPG2408TB	SPDT, 3V, 0.50dB Insertion Loss, High ESD immunity
UPG2409TB	SPDT 2.0 – 4.0GHz, Insertion Loss: 0.45dB @ 2.5GHz, 0.6dB @ 3.8GHz
UPG2406TK	SPDT, 1.8 or 2.7V control voltage, 0.45dB Insertion Loss @ 2GHz, High ESD immunity
NEW CKRF2406XS02	SPDT, Cost-effective, Lowest Insertion Loss: 0.25dB @ 2.5GHz, small thin package
NEW CKRF2179MM26	SPDT, Medium power, Insertion Loss: 0.30dB @ 2.5GHz
NEW CKRF2413XS01	SP3T, Cost-effective, Insertion Loss: 0.35dB @ 2.5GHz

GaAs RFIC Switches to 6GHz

UPG2422TK	SPDT for Dual Band WLAN, 1.8-5.3V control voltage range
UPG2163T5N	SPDT, Insertion Loss: 0.4dB @ 2.4GHz, 0.5dB @ 6GHz, Isolation = 30dB @ 6GHz
UPG2176T5N	SPDT 2.4 – 6GHz, Insertion Loss: 0.5dB @ 2.4GHz, 0.7dB @ 5.5GHz, internal terminations
UPG2415TK / T6X	SPDT for Dual Band WLAN, high power, low insertion loss for Access Point applications
UPG2409T6X	SPDT for Dual Band WLAN, highest power, low insertion loss for Access Point applications
NEW CKRF2185XS02	SPDT for Dual Band WLAN, cost-effective, Insertion Loss: 0.5dB @ 6GHz, small thin package
NEW CKRF2430XS01	SP3T, Insertion Loss: 0.55dB @ 6GHz, Isolation = 25dB @ 6GHz
UPG2164T5N	DPDT, Insertion Loss: 0.7dB @ 6GHz, 17dB Isolation @ 6GHz
UPG2162T5N	DPDT, Insertion Loss: 0.85dB @ 6GHz, 27dB Isolation @ 6GHz

RF Switch ICs

SPDTs (Single Pole Double Throw)

Part Number	PLP ³	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25°C)						Pkg. Code ⁴	Description
		Frequency (GHz, max)	Control Voltages (V)	Insertion Loss (dB)	Isolation (dB)	Input Power @ 0.1 dB compression point (dBm)	Input Power @ 1.0 dB compression point (dBm)		
UPD5713TK ¹		2.5	+1.8, 2.8/0	0.80 @ 2 GHz	25 @ 2 GHz	+17	+21	TK	Single Control (1.8-V _{dd}), small size package, CMOS
UPG2009TB ¹		3.0	+2.8/0	0.30 @ 2 GHz	28 @ 2 GHz	+34	–	TB	High power handling, low insertion loss, high isolation
UPG2030TK ¹		3.0	+2.8/0	0.30 @ 2 GHz	27 @ 2 GHz	+27	+30	TK	Medium power, small size package
UPG2155TB ¹		2.5	+2.6/0	0.40 @ 2 GHz	19 @ 2 GHz	+37	–	TB	High power handling, low harmonics, lowest cost high power switch
UPG2163T5N ¹		8.0	+3.0/0	0.4 @ 2.5 GHz 0.5 @ 6 GHz	35 @ 2.5 GHz 30 @ 6 GHz	–	+35 @ 2.5 GHz +29 @ 6 GHz	T5N	Highest isolation, great 2.4 and 6 GHz performance
UPG2176T5N ¹		6.0	+3.0/0	0.55 @ 3.5 GHz	24 @ 3.5 GHz	–	+37	T5N	Absorptive, high power and high linearity to 6 GHz
UPG2214TB ¹		3.0	+1.8, 3.0/0	0.30 @ 2 GHz	27 @ 2 GHz	+23	+20 (1.8 V), 26 (3.0 V)	TB	Low insertion loss, high isolation, medium power, 1.8V-5.3V.
UPG2214TK ¹		3.0	+1.8, 3.0/0	0.30 @ 2 GHz	27 @ 2 GHz	+23	+20 (1.8 V), 26 (3.0 V)	TK	Small size package, low insertion loss, high isolation, medium power, 1.8V-5.3V.
UPG2406TK ¹		3.0	+1.8, 2.7/0	0.45 @ 2 GHz	19 @ 2 GHz	+29	+25 (1.8 V), 30.5 (3.0 V)	TK	Small size package, cost effective medium power, 1.8V-5.3V
UPG2408TB ¹		3.0	+3.0/0	0.48 @ 2 GHz	19 @ 2 GHz	+29	–	TB	Low cost medium power for UHF-3 GHz
UPG2408TK ¹		3.0	+3.0/0	0.48 @ 2 GHz	19 @ 2 GHz	+29	–	TK	Small size package, cost effective medium power
UPG2409TB ¹		3.8	+3.0/0	0.45 @ 2.5 GHz 0.60 @ 3.8 GHz	26 @ 2.5 GHz 19 @ 3.8 GHz	+33.5	+35	TB	Low Cost high power SPDT, for Access Points to 3.8 GHz
UPG2409T6X ¹		6.0	+3.0/0	0.45 @ 2.5 GHz 0.65 @ 6 GHz	30 @ 2.5 GHz 27 @ 6 GHz	+34	+36	T6X	High power, for Access Points to 6 GHz, 1.5mm QFN package
UPG2415TK ¹		6.0	+3.0/0	0.45 @ 2.5 GHz 0.65 @ 6 GHz	28 @ 2.5 GHz 26 @ 6 GHz	+31	+34	TK	High power handling for Access Points to 6 GHz, small size package
UPG2415T6X ¹		6.0	+3.0/0	0.45 @ 2.5 GHz 0.55 @ 6 GHz	28 @ 2.5 GHz 26 @ 6 GHz	+31	+35	T6X	High power handling for Access Points to 6 GHz, 1.5mm QFN package
UPG2422TK ¹		6.0	+1.8, 3.0/0	0.35 @ 2.5 GHz, 0.55 @ 6 GHz	28 @ 2.5 GHz 24 @ 6 GHz	+28 @ 2-6 GHz	+31 @ 6 GHz	TK	Low cost 6 GHz SPDT, medium power, small size package, low insertion loss, high isolation, 1.8V-5.3V
 CKRF2159XS02 ²	–	3.0	+1.8, 3.0/0	0.25 @ 2.5 GHz	27 @ 2.5 GHz	+22	+25.5	XS02	Low Cost, Lowest Insertion Loss, small thin package
 CKRF2185XS02 ²	–	6.0	+1.8, 3.0/0	0.40 @ 2.5 GHz 0.5 @ 6 GHz	26 @ 2.5 GHz 25 @ 6 GHz	+29	+30.5	XS02	Low Cost SPDT specified to 6 GHz with a small thin package
 CKRF2406XS02 ²	–	3.0	+1.8, 3.0/0	0.25 @ 2.5 GHz	17 @ 2.5 GHz	+29	+30.5	XS02	Low Cost, Lowest Insertion Loss, small thin package
 CKRF2179MM26 ²	–	3.0	+1.8, 3.0/0	0.30 @ 2.5 GHz	27 @ 2.5 GHz	+28	+31	MM26	Low cost, Low insertion loss, Medium Power SPDT

Notes: 1. Manufactured by Renesas Electronics 2. Manufactured by CDK (Chou Denshi Kogyo), a longtime manufacturing partner for Renesas Electronics. Contact CEL for production status
3. See Product Longevity Program details on page 12 4. See Package Dimensions on page 11

RF Switch ICs continued

SP3Ts (Single Pole Triple Throw)

Part Number ¹	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25°C)						Package Code ²	Description
	Frequency (GHz, max)	Control Voltages (V)	Insertion Loss (dB)	Isolation (dB)	Input Power @0.1 dB compression point (dBm)	Input Power @1.0 dB compression point (dBm)		
 CKRF2413XS01	3.0	+1.8, 3.0/0	0.35 @ 2.5GHz	18 @ 2.5GHz	+28	+31	XS01	Lowest Cost SP3T, Low Insertion Loss
 CKRF2430XS01	6.0	+1.8, 3.0/0	0.50 @ 2.5GHz 0.55 @ 6GHz	28 @ 2.5GHz 25 @ 6GHz	+28	+31	XS01	SP3T specified to 6GHz with high isolation

Notes: 1. Manufactured by CDK (Chou Denshi Kogyo), a longtime manufacturing partner for Renesas Electronics. Contact CEL for production status 2. See Package Dimensions on page 11

DPDTs (Double Pole Double Throw)

Part Number ¹	PLP ²	TYPICAL ELECTRICAL CHARACTERISTICS (T _A = 25°C)						Package Code ³	Description
		Frequency (GHz, max)	Control Voltages (V)	Insertion Loss (dB)	Isolation (dB)	Input Power @0.1 dB compression point (dBm)	Input Power @1.0 dB compression point (dBm)		
UPG2164T5N		6.0	+3.0/0	0.5 @ 2.4GHz 0.7 @ 5.5GHz	25 @ 2.4GHz 17 @ 5.5GHz	–	+31 +29	T5N	Lowest cost, lowest insertion loss DPDT. 6GHz operation.
UPG2162T5N		6.0	+3.0/0	0.6 @ 2.4GHz 0.85 @ 5.5GHz	30 @ 2.4GHz 27 @ 5.5GHz	–	+31 +29	T5N	Best isolation of all DPDTs, up to 6GHz operation
UPD5738T6N		2.5	+2.8/0	0.8 @ 1GHz	22 @ 1GHz	+15	+20	T6N	Only one control pin, low frequency operation, CMOS, 1.5V-3.6V

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

GaAs FETs

Low Noise GaAs FETs, 1 to 20GHz Typical Specifications @ T_A = 25°C

Part Number ¹	PLP ²	Gate Length (μm)	Gate Width (μm)	Recommended Frequency Range (GHz)	Test Frequency (GHz)	NF/GA Bias		NF _{OPT} (dB)	G _A (dB)	Power Bias		P _{1dB} (dBm)	Package Code ³	Package Description
						V _{DS} (V)	I _{DS} (mA)			V _{DS} (V)	I _{DS} (mA)			
NE3503M04		0.2	160	2 to 18	12	2.0	10	0.55	11.5	–	–	–	M04	Plastic SMD
NE3508M04		0.6	800	1 to 6	2	2.0	10	0.40	14.0	3.0	30	+18.0	M04	Plastic SMD
NE3509M04		0.6	400	1 to 6	2	2.0	10	0.45	17.5	3.0	20	+14.0	M04	Plastic SMD
NE3510M04		0.6	280	1 to 6	2	2.0	10	0.35	19.0	3.0	30	+12.0	M04	Plastic SMD
NE3511S02		0.2	160	4 to 18	12	2.0	10	0.30	13.5	–	–	–	S02	Micro-X Plastic
NE3512S02		0.2	160	4 to 18	12	2.0	10	0.35	13.5	–	–	–	S02	Micro-X Plastic
NE3513M04		0.2	160	10 to 14	12	2.0	6	0.45	13.0	–	–	–	M04	Plastic SMD
NE3514S02		0.2	160	4 to 20	20	2.0	10	0.75	10.0	–	–	–	S02	Micro-X Plastic
NE3515S02		0.2	200	6 to 18	12	2.0	10	0.3	12.5	3.0	25	+14.0	S02	Micro-X Plastic
NE3516S02		0.2	160	6 to 18	12	2.0	10	0.35	14.0	–	–	–	S02	Plastic SMD
NE3520S03		–	160	10 to 26	20	2.0	10	0.65	13.5	–	–	–	S03	Micro-X Plastic
NE3521M04		–	–	10 to 26	20	2.0	10	0.85	11	–	–	–	M04	Plastic SMD

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

Silicon MOSFET Devices

RF Power LD-MOSFETs Typical Specifications @ T_c = 25°C

Part Number ¹	PLP ²	P _{OUT} (dBm) TYP	Linear Gain (dB) TYP	Test Conditions				Package Code ³	Package Description
				Freq (GHz)	P _{IN} (dBm)	V _{DS} (V)	I _{DSQ} (mA)		
NE5550234	rf	+33 +32.2	23.5 18.3	0.46 0.90	+15 +17	7.5 7.5	40 40	34	Plastic SMD
NE5550279A	rf	+33	22.5	0.46	+15	7.5	40	79A	Plastic SMD
NE5550779A	rf	+38.5 +37.4	22 17	0.46 0.90	+25 +27	7.5 7.5	140 140	79A	Plastic SMD
NE5550979A	rf	+39.5 +38.6	22 16	0.46 0.90	+25 +27	7.5 7.5	200 200	79A	Plastic SMD
NE5531079A	—	+40.0	20.5	0.46	+25	7.5	200	79A	Plastic SMD

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

MOSFET for Microphone Impedance Conversion

Part Number ¹	PLP ²	Supply Voltage (V)	Circuit Current (μA)	Input Capacitance (pF)	Voltage Gain (dB)	Output Noise Voltage (dBV)	Total Harmonic Distortion (%)	HBM ESD (KV)	Package Code ³
NE5820M53	rf	2	85	1.5	-3	-114	0.1	>8	M53

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

Silicon Bipolar Transistors

Small Signal Silicon Devices

Part Number ¹	Equivalent Part Number	PLP ²	TEST f (GHz)	NF/GA		NF TYP (dB)	GA TYP (dB)	MAG/MSG			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Package Code ³	Package Style
				V _{CE} (V)	I _{CQ} (mA)			V _{CE} (V)	I _C (mA)	TYP (dB)					
NE202930	–	PLP	1.0	5	5	1.15	13.5	5	30	15.5	11	140	100	30	SOT-323
NE662M04	2SC5508	PLP	2.0	2	5	1.1	16	2	20	20	23	70	35	M04	SOT-343F
NE66219	2SC5606	PLP	2.0	2	5	1.5	12.0	2	20	14	21	80	35	19	SC-90
NE68018	2SC5013	PLP	2.0	6	5	1.8	10.0	1	1	12.5	10	100	35	18	SOT-343
NE68019	2SC5008	PLP	2.0	3	5	1.9	9.0	1	1	12.0	8	120	35	19	SC-90
NE68030	2SC4228	PLP	2.0	6	5	1.7	9.5	6	10	8.5	10	100	35	30	SOT-323
NE68033	2SC3585	PLP	2.0	6	5	1.8	9.0	6	10	8.0	10	100	35	33	SOT-23
NE68039	2SC4095	–	2.0	6	5	1.7	11.0	6	10	9.0	10	100	35	39	SOT-143
NE68118	2SC5012	–	1.0	2.5	3	1.1	13.0	2.5	3	16.0	9	100	65	18	SOT-343
NE68119	2SC5007	PLP	1.0	2.5	3	1.1	12.0	2.5	3	15.5	7	120	65	19	SC-90
NE68130	2SC4227	PLP	1.0	8	7	1.5	13.5	8	20	13.0	7	120	65	30	SOT-323
NE68133	2SC3583	PLP	1.0	8	7	1.2	13.0	8	20	11.0	9	100	65	33	SOT-23
NE68139	2SC4094	–	1.0	8	7	1.2	13.5	8	20	15.0	9	100	65	39	SOT-143
NE68518	2SC5015	PLP	2.0	2.5	3	1.5	8.5	2.5	3	12.0	12	110	30	18	SOT-343
NE68519	2SC5010	PLP	2.0	2.5	3	1.5	7.5	2.5	3	11.0	12	110	30	19	SC-90
NE85618	2SC5011	–	1.0	2.5	3	1.4	11.0	2.5	3	14.0	6.5	120	100	18	SOT-343
NE85619	2SC5006	PLP	1.0	2.5	3	1.5	10.0	2.5	3	13.5	4.5	120	100	19	SC-90
NE85630	2SC4226	PLP	1.0	10	7	1.3	12.0	10	20	12.0	4.5	110	100	30	SOT-323
NE85633	2SC3356	PLP	1.0	10	7	1.4	9.0	10	20	11.5	7	120	100	33	SOT-23
NE85639	2SC4093	PLP	1.0	10	7	1.5	13.5	10	20	13.0	7	120	100	39	SOT-143
NE97733	2SA1977	–	1.0	–8	–3	1.5	10.0	–8	–20	12.0	8.5	60	–50	33	SOT-23
NE97833	2SA1978	–	1.0	–10	–3	2.0	7.0	–10	–15	10.0	5.5	40	–50	33	SOT-23
2SA1977	NE97733	–	1.0	–8	–3	1.5	10.0	–8	–20	12.0	8.5	60	–50	33	SOT-23
2SA1978	NE97833	–	1.0	–10	–3	2.0	7.0	–10	–15	10.0	5.5	40	–50	33	SOT-23
2SC3356	NE85633	PLP	1.0	10	7	1.4	9.0	10	20	11.5	7	120	100	33	SOT-23
2SC3583	NE68133	PLP	1.0	8	7	1.2	13.0	8	20	11.0	9	100	65	33	SOT-23
2SC3585	NE68033	PLP	2.0	6	5	1.8	9.0	6	10	8.0	10	100	35	33	SOT-23
2SC4093	NE85639	PLP	1.0	10	7	1.5	13.5	10	20	13.0	7	120	100	39	SOT-143
2SC4094	NE68139	–	1.0	8	7	1.2	13.5	8	20	15.0	9	100	65	39	SOT-143
2SC4095	NE68039	–	2.0	6	5	1.7	11.0	6	10	9.0	10	100	35	39	SOT-143
2SC4226	NE85630	PLP	1.0	10	7	1.3	12.0	10	20	12.0	4.5	110	100	30	SOT-323
2SC4227	NE68130	PLP	1.0	8	7	1.5	13.5	8	20	13.0	7	120	65	30	SOT-323
2SC4228	NE68030	PLP	2.0	6	5	1.7	9.5	6	10	8.5	10	100	35	30	SOT-323
2SC5006	NE85619	PLP	1.0	2.5	3	1.5	10.0	2.5	3	13.5	4.5	120	100	19	SC-90
2SC5007	NE68119	PLP	1.0	2.5	3	1.1	12.0	2.5	3	15.5	7	120	65	19	SC-90
2SC5008	NE68019	PLP	2.0	3	5	1.9	9.0	1	1	12.0	8	120	35	19	SC-90
2SC5010	NE68519	PLP	2.0	2.5	3	1.5	7.5	2.5	3	11.0	12	110	30	19	SC-90
2SC5011	NE85618	–	1.0	2.5	3	1.4	11.0	2.5	3	14.0	6.5	120	100	18	SOT-343
2SC5012	NE68118	–	1.0	2.5	3	1.1	13.0	2.5	3	16.0	9	100	65	18	SOT-343
2SC5013	NE68018	PLP	2.0	6	5	1.8	10.0	1	1	12.5	10	100	35	18	SOT-343
2SC5015	NE68518	PLP	2.0	2.5	3	1.5	8.5	2.5	3	12.0	12	110	30	18	SOT-343
2SC5508	NE662M04	PLP	2.0	2	5	1.1	16	2	20	20	23	70	35	M04	SOT-343F
2SC5606	NE66219	PLP	2.0	2	5	1.5	12.0	2	20	14	21	80	35	19	SC-90

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

Silicon Bipolar Transistors continued

Medium Power Transistors

Part Number ¹	Equivalent Part Number	PLP ²	TEST f (GHz)	P _{1dB}			MAG / MSG			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Package Code ³	Package Style
				V _{CE} (V)	I _{CQ} (mA)	TYP (dBm)	V _{CE} (V)	I _C (mA)	TYP (dB)					
NE46134	2SC4536	PLP	1.0	12.5	100	27.5	10	50	9	5.5	100	250	34	SOT-89
NE461M02	2SC5337	PLP	1.0	12.5	100	27.5	10	50	11	5.5	120	250	M02	SOT-89
NE663M04	2SC5509	–	2.0	2	50	16	2	50	15	18	100	100	M04	SOT-343F
NE664M04	2SC5754	PLP	1.8	3.6	200	26	3	100	12	20	60	500	M04	SOT-343F
NE677M04	2SC5751	–	1.8	2.8	23	15	3	20	16	15	120	50	M04	SOT-343F
NE678M04	2SC5753	PLP	1.8	2.8	40	18	3	30	13.5	12	120	100	M04	SOT-343F
NE85634	2SC3357	PLP	1.0	10	40	22	10	40	11	6.5	120	100	34	SOT-89
NE856M02	2SC5336	PLP	1.0	10	40	22	10	50	14	6.5	120	100	M02	SOT-89
2SC3357	NE85634	PLP	1.0	10	40	22	10	40	11	6.5	120	100	34	SOT-89
2SC4536	NE46134	PLP	1.0	12.5	100	27.5	10	50	9	5.5	100	250	34	SOT-89
2SC5336	NE856M02	PLP	1.0	10	40	22	10	50	14	6.5	120	100	M02	SOT-89
2SC5337	NE461M02	PLP	1.0	12.5	100	27.5	10	50	11	5.5	120	250	M02	SOT-89
2SC5509	NE663M04	–	2.0	2	50	16	2	50	15	18	100	100	M04	SOT-343F
2SC5751	NE677M04	–	1.8	2.8	23	15	3	20	16	15	120	50	M04	SOT-343F
2SC5753	NE678M04	PLP	1.8	2.8	40	18	3	30	13.5	12	120	100	M04	SOT-343F
2SC5754	NE664M04	PLP	1.8	3.6	200	26	3	100	12	20	60	500	M04	SOT-343F

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

Twin Transistors

Part Number ¹	PLP ²	TEST f (GHz)	NF/G _A V _{CE} (V)	NF/G _A I _C (mA)	NF TYP (dB)	G _A TYP (dB)	MAG (dB)	IS _{21E} I			f _T TYP (GHz)	h _{FE} TYP	I _C MAX (mA)	Die	Pkg. Code ³	Package Style
								V _{CE} (V)	I _C (mA)	TYP (dB)						
UPA800T	–	2.0	3	5	1.9	9.0	12.0	3	5	7.5	8	120	35	2 each NE680	T	SOT-363
UPA801T	PLP	1.0	3	7	1.2	10.0	14.0	3	7	9.0	4.5	120	100	2 each NE856	T	SOT-363
UPA802T	–	1.0	3	7	1.4	14.0	16.0	3	7	12.0	7.0	100	65	2 each NE681	T	SOT-363
UPA806T	PLP	2.0	3	3	1.5	7.5	11.0	3	10	8.5	12.0	110	30	2 each NE685	T	SOT-363
UPA810T	–	1.0	3	7	1.2	10.0	14.0	3	7	9.0	4.5	120	100	2 each NE856	T	SOT-363
UPA811T	–	2.0	3	5	1.9	9.0	12.0	3	5	7.5	8	120	35	2 each NE680	T	SOT-363

Notes: 1. Manufactured by Renesas Electronics 2. See Product Longevity Program details on page 12 3. See Package Dimensions on page 11

3V Silicon MMIC Amplifiers

Part Number ⁶	PLP ⁷	Typical Frequency Range @ 3dB down (MHz)	ELECTRICAL CHARACTERISTICS ¹ (T _A = 25°C)												Package Code ⁸	Package Style
			V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)			RL _{IN} (dB)	RL _{OUT} (dB)	P _{1dB} (dBm)	ISOL (dB)		
				MIN	TYP	MAX	TYP	MIN	TYP	MAX	TYP	TYP	TYP	TYP		
UPC2745TB ²	Ⓢ	2700	3	5	7.5	10	6.0	9	12	14	11	5.5	-3.0	38	TB	SOT-363
UPC2746TB ²	Ⓢ	1500	3	5	7.5	10	4.0	16	19	21	13	8.5	-3.7	45	TB	SOT-363
UPC2748TB ³	Ⓢ	1500	3	4.5	6	8	2.8	16	19	21	11.5	8.5	-8.5	40	TB	SOT-363
UPC2749TB ⁴	Ⓢ	2900	3	4	6	8	4	13	16	18.5	10	13	-12.5	30	TB	SOT-363
UPC2762TB ⁴	Ⓢ	2900	3	–	27	35	7.0	11.5	15.5	17.5	8.5	12	+7	25	TB	SOT-363
UPC8178TK ⁴	Ⓢ	2700	3	1.4	1.9	2.4	5.5	9.0	11.0	13.5	8	–	-8.0	41	TK	6 pin Recessed Lead
UPC8179TK ⁴	Ⓢ	Note 5	3	2.9	4.0	5.4	5.0	13.0	15.5	17.5	7	–	0.5	42	TK	6 pin Recessed Lead

Notes: 1. Z_L = 50 Ω for all Electrical Characteristics 2. f = 500 MHz test condition 3. f = 900 MHz test condition 4. f = 1900 MHz test condition
5. 100–2400MHz with output port matching 6. Manufactured by Renesas Electronics 7. See Product Longevity Program details on page 12
8. See Package Dimensions on page 11

5V Silicon MMIC Amplifiers

Part Number ⁴	PLP ⁵	Typical Frequency Range @ 3dB down (MHz)	ELECTRICAL CHARACTERISTICS ¹ (T _A = 25°C)												Package Code ⁶	Package Style
			V _{CC} (V)	I _{CC} (mA)			NF (dB)	Gain (dB)			RL _{IN} (dB)	RL _{OUT} (dB)	P _{1dB} (dBm)	ISOL (dB)		
				MIN	TYP	MAX	TYP	MIN	TYP	MAX	TYP	TYP	TYP	TYP		
UPC2708TB ³	Ⓢ	2900	5	20	26	33	6.5	13	15	18.5	11	20	+9.2	23	TB	SOT-363
UPC2709TB ³	Ⓢ	2300	5	19	25	32	5.0	21	23	26.5	10	10	+8.7	31	TB	SOT-363
UPC2710TB ²	Ⓢ	1000	5	16	22	29	3.5	30	33	36.5	6	12	+10.8	39	TB	SOT-363
UPC3223TB ³	Ⓢ	3200	5	15	19	24	4.5	20.5	23	22.5	12	12	+6.5	33	TB	SOT-363
UPC3224TB ³	Ⓢ	3200	5	7.0	9.0	12.0	4.3	19	21.5	24	12	17	-3.5	40	TB	SOT-363

Notes: 1. Z_L = 50 Ω for all Electrical Characteristics 2. f = 500 MHz test condition 3. f = 1000 MHz test condition 4. Manufactured by Renesas Electronics
5. See Product Longevity Program details on page 12 6. See Package Dimensions on page 11

Frequency Upconverters

Part Number ⁴	PLP ⁵	ELECTRICAL CHARACTERISTICS (T _A = 25°C)								Package Code ⁶	Package Style
		IF Input Frequency Range @3 dB Down (MHz)	RF Output Frequency Range (MHz)	V _{CC} (V)	I _{CC} (mA)	Conversion Gain (dB)	P _{SAT} ¹ (dBm)	Noise Figure (dB)	OIP ₃		
		TYP	TYP								
UPC8106TB ²		50-400	400-2000	3.0	9.0	10.0	-2.0	8.5	+5.5	TB	SOT-363
UPC8172TB ³		50-400	800-2500	3.0	9.0	8.5	0.0	10.4	+6.0	TB	SOT-363

Notes: 1. PIN = 0 dBm 2. RF = 900 MHz, LO = 660 MHz, PLO = -5 dBm 3. RF = 1900 MHz, LO = 1660 MHz, PLOIN = -5 dBm 4. Manufactured by Renesas Electronics
5. See Product Longevity Program details on page 12 6. See Package Dimensions on page 11

Frequency Downconverters

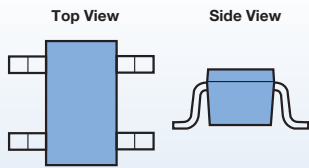
Part Number ²	PLP ³	ELECTRICAL CHARACTERISTICS (T _A = 25°C)								Package Code ⁴	Package Style
		RF Input Frequency Range @3 dB Down (MHz)	IF Output Frequency Range @3 dB Down (MHz)	V _{CC} (V)	I _{CC} (mA)	Conversion Gain (dB)	P _{SAT} (dBm)	Noise Figure (dB)	Test Condition (Note)		
		TYP	TYP								
UPC2756TB		100-2000	10-300	3.0	5.9	14	-12	13	3	TB	SOT-363
UPC2757TB ¹		100-2000	20-300	3.0	5.6	13	-8	13	4	TB	SOT-363
UPC2758TB ¹		100-2000	20-300	3.0	11	17	-4	13	4	TB	SOT-363
UPC8112TB ¹		800-2000	100-300	3.0	8.5	13	-3	11.2	5	TB	SOT-363

Note: 1. AGC Amp and Mixer Block only 2. Manufactured by Renesas Electronics 3. See Product Longevity Program details on page 12 4. See Package Dimensions on page 11

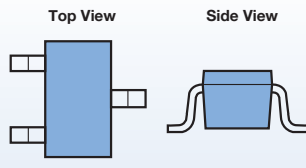
Package Dimensions Units in mm

These dimensions are for the package only. For detailed dimensions including leads, please refer to the datasheet.

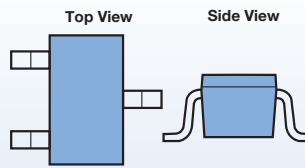
18 Package (1.25 x 2.0 x 0.9)



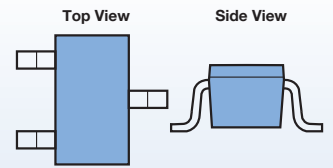
19 Package (0.8 x 1.6 x 0.75)



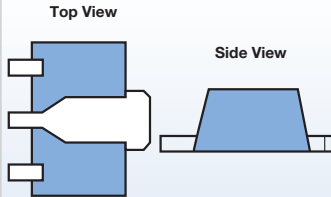
30 Package (1.25 x 2.0 x 0.9)



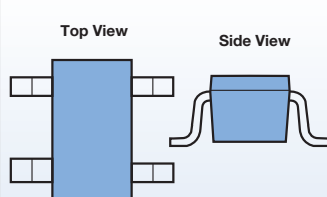
33 Package (1.5 x 2.9 x 1.4)



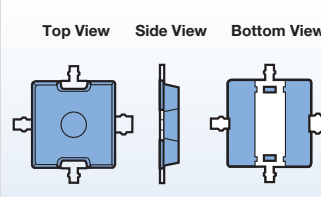
34 Package (2.5 x 4.5 x 1.5)



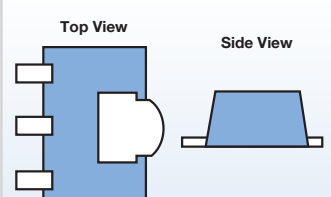
39 Package (1.5 x 2.9 x 1.1)



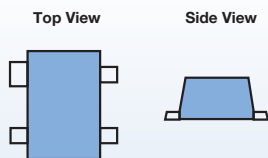
79A Package (4.2 x 4.4 x 0.9)



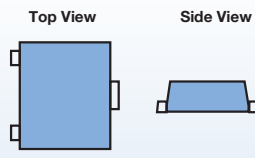
M02 Package (2.45 x 4.5 x 1.5)



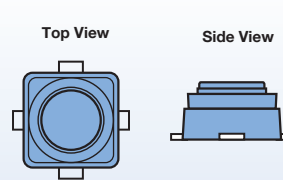
M04 Package (1.25 x 2.0 x 0.6)



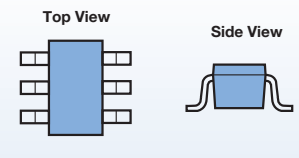
M53 Package (1.0 x 1.2 x 0.33)



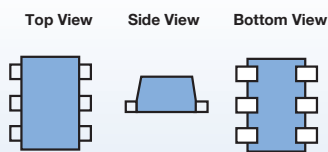
S02 / S03 Package (2.6 x 2.6 x 1.5)



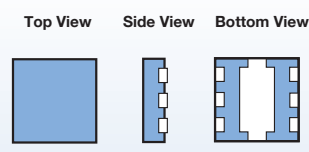
T / TB / MM26 Package (1.25 x 2.0 x 0.9)



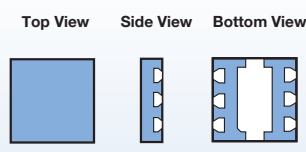
TK Package (1.1 x 1.5 x 0.55)



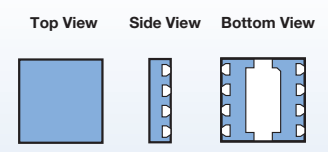
T5N / T6N Package (1.5 x 1.5 x 0.37)



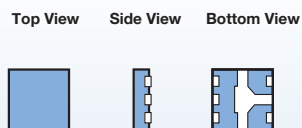
T6X Package (1.5 x 1.5 x 0.37)



XS01 Package (1.5 x 1.5 x 0.37)



XS02 Package (1.0 x 1.0 x 0.37)



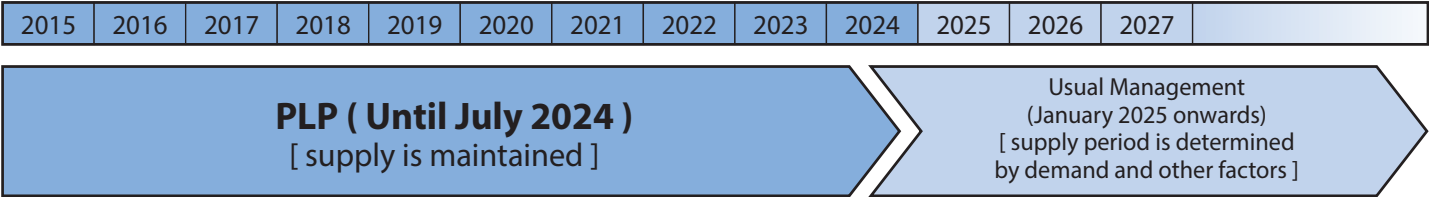
Product Longevity Program



Program Overview

California Eastern Laboratories, Inc. is pleased to announce the Product Longevity Program to our customers purchasing Renesas Electronics products. The parts selected for participation in this program are planned to have a long production life cycle.

Planned Life Cycle for PLP Products



Program Details

1. Products participating in this program are expected to have a long product life.

2. A list of the products participating in this program is provided via the link below.

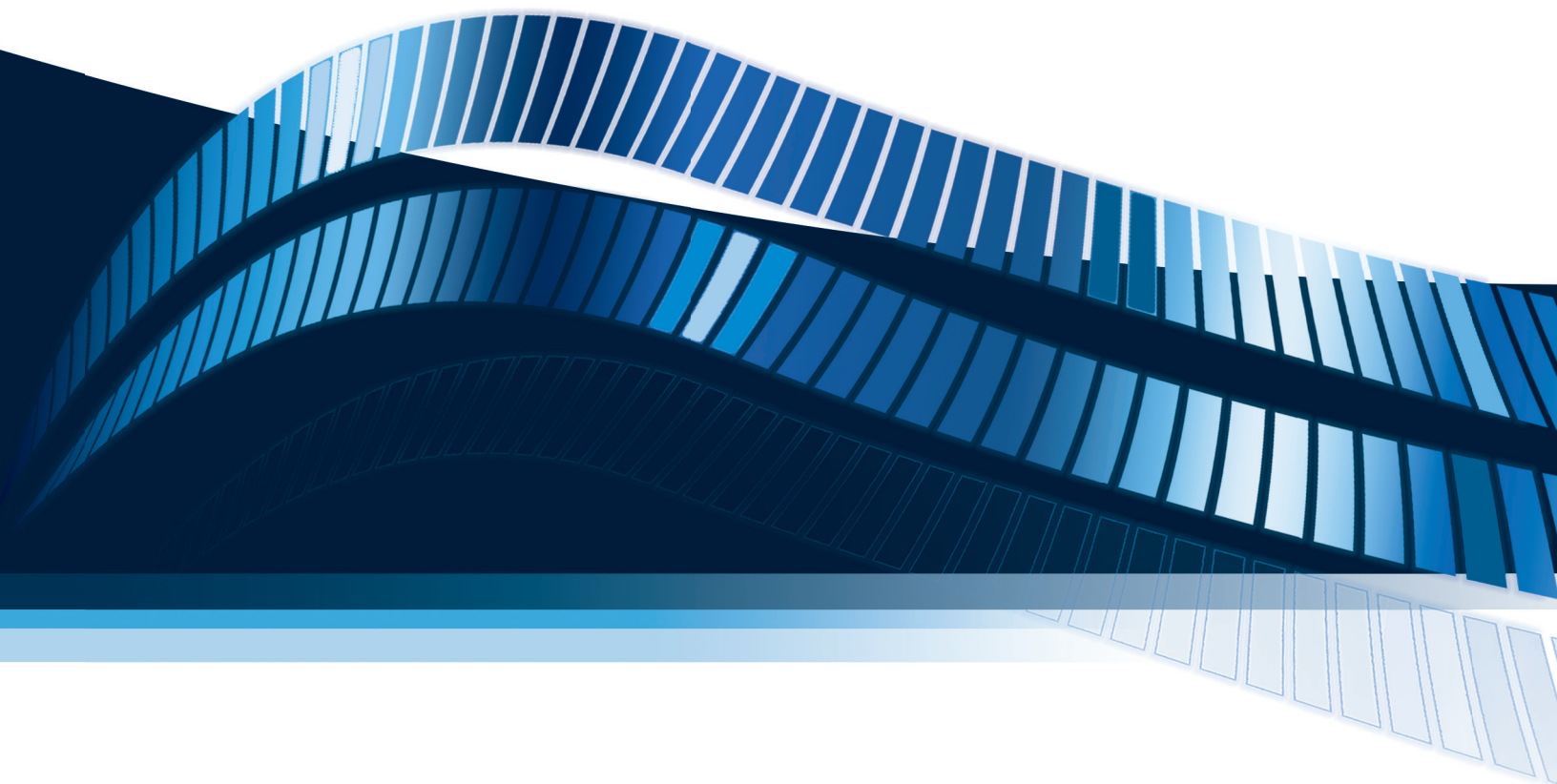
3. The products in this program are clearly identified with the PLP icon .

4. Due to various circumstances, in some cases a PLP product may be replaced by an equivalent product that is also in the PLP.
5. PCN (Product Change Notices) for changes in product specifications, manufacturing facilities, or materials may be issued due to circumstances beyond our control even while this program is in effect.

6. The date of PLP termination is the date that was planned at the point in time when it was officially announced. It is subject to change.

For complete PLP Part List and up to date information
Please visit us at:

www.cel.com/plp



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